

1A, 50V - 600V Surface Mount Ultrafast Power Rectifier

FEATURES

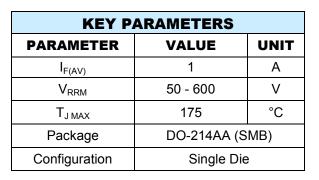
- Glass passivated chip junction
- Ideal for automated placement
- Ultrafast recovery time for high efficiency
- Low forward voltage, low power loss
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

Δ	D	DI	IC	ın	PI

- Switching mode power supply (SMPS)
- Adapters
- Lighting application
- Converter

MECHANICAL DATA

- Case: DO-214AA (SMB)
- Molding compound meets UL 94V-0 flammability rating
- Moisture sensitivity level: level 1, per J-STD-020
- Packing code with suffix "G" means green compound (halogen-free)
- Part no. with suffix "H" means AEC-Q101 qualified
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 0.09 g (approximately)







DO-214AA (SMB)

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)								
PARAMETER	SYMBOL	MUR 105S	MUR 110S	MUR 115S	MUR 120S	MUR 140S	MUR 160S	UNIT
Marking code on the device		MUR 105S	MUR 110S	MUR 115S	MUR 120S	MUR 140S	MUR 160S	
Repetitive peak reverse voltage	V_{RRM}	50	100	150	200	400	600	V
Reverse voltage, total rms value	$V_{R(RMS)}$	35	70	105	140	280	420	V
Maximum DC blocking voltage	V _{DC}	50	100	150	200	400	600	V
Forward current	I _{F(AV)}				1			Α
Surge peak forward current, 8.3 ms single half sine-wave superimposed on rated load per diode	I _{FSM}	40 35			5	А		
Junction temperature	TJ	- 55 to +175				°C		
Storage temperature	T _{STG}		- 55 to +175					°C

1





THERMAL PERFORMANCE						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-lead thermal resistance	$R_{\Theta JL}$	17	°C/W			

PARAMETER	CONDITIONS	SYMBOL	TYP	MAX	UNIT	
	MUR105S					V
	MUR110S			-	0.875	V
Forward voltage per diode (1)	MUR115S	I _F = 1A,T _J = 25°C	V_{F}			V
i oiwaid voitage per diode	MUR120S	IF = IA, IJ = 25 0	٧٢			V
	MUR140S			_	1.250	V
	MUR160S					V
	MUR105S					V
	MUR110S			-	0.710	V
Forward voltage per diode (1)	MUR115S	I _F = 1A,T _J = 150°C	V_{F}			V
•	MUR120S					V
	MUR140S MUR160S			-	1.050	V
		T _J = 25°C		-	2	
	MUR105S					μΑ
	MUR110S					μA
Reverse current @ rated V _R per diode ⁽²⁾	MUR115S		I_R			μA
per diode 17	MUR120S				5	μA
	MUR140S			-		μA
	MUR160S					μA
	MUR105S	_ - - T _J = 150°C	I _R	-	50	μA
	MUR110S					μA
Reverse current @ rated V _R	MUR115S					μA
per diode (2)	MUR120S		אי			μA
	MUR140S		-	_	150	μA
	MUR160S			_		μA
	MUR105S					ns
	MUR110S	I _F =0.5A ,I _R =1.0A			25	ns
D	MUR115S		t _{rr}	-		ns
Reverse recovery time	MUR120S	I _{RR} =0.25A				ns
	MUR140S			-	50	ns
	MUR160S					ns

Notes:

- 1. Pulse test with PW=0.3 ms
- 2. Pulse test with PW=30 ms



Taiwan Semiconductor

ORDERING INFORMATION								
PART NO.	PART NO. SUFFIX	PACKING CODE	PACKING CODE SUFFIX(*)	PACKAGE	PACKING			
		R5		SMB	850 / 7" Plastic reel			
MUR1xxS (Note 1)	Н	R4	G	SMB	3,000 / 13" Paper reel			
(11010 1)		M4		SMB	3,000 / 13" Plastic reel			

Note:

^{*:} Optional available

EXAMPLE P/N							
EXAMPLE P/N	PART NO.	PART NO. SUFFIX	PACKING CODE	PACKING CODE SUFFIX	DESCRIPTION		
MUR160SHR5G	MUR160S	Н	R5	G	AEC-Q101 qualified Green compound		

^{1. &}quot;x" defines voltage from 50V (MUR105S) to 1000V (MUR160S)



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig1. Forward Current Derating Curve

1.5 VERYARD CURRENT (°C)

Fig2. Typical Junction Capacitance

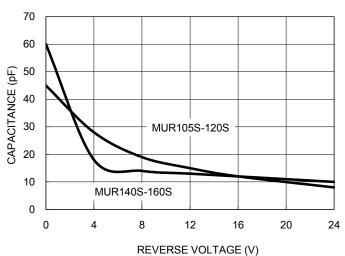


Fig3. Typical Reverse Characteristics

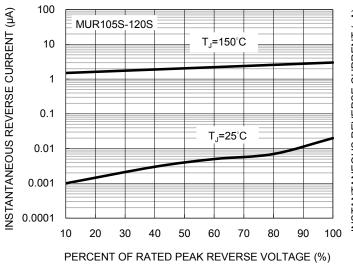
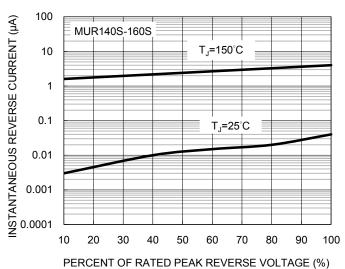


Fig4. Typical Reverse Characteristics



4



Fig5. Typical Forward Characteristics

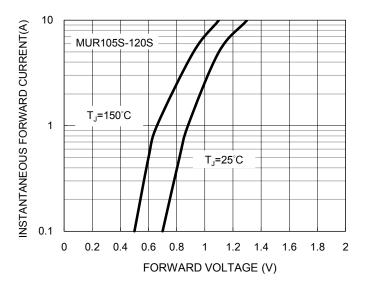


Fig6. Typical Forward Characteristics

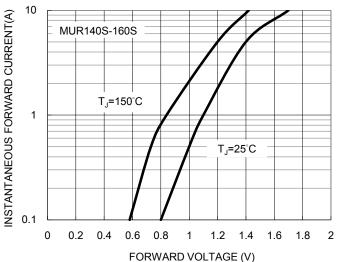
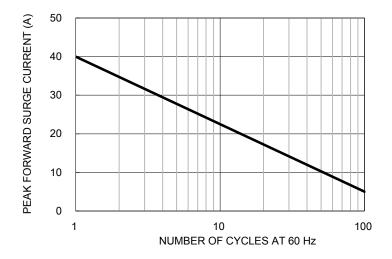


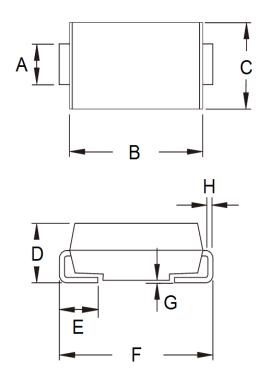
Fig5. Maximum Non-repetitive Forward Surge Current





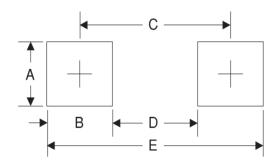
PACKAGE OUTLINE DIMENSIONS

DO-214AA (SMB)



DIM.	Unit	(mm)	Unit (inch)		
DIWI.	Min	Max	Min	Max	
Α	1.95	2.20	0.077	0.087	
В	4.05	4.60	0.159	0.181	
С	3.30	3.95	0.130	0.156	
D	1.95	2.65	0.077	0.104	
Е	0.75	1.60	0.030	0.063	
F	5.10	5.60	0.201	0.220	
G	0.05	0.20	0.002	0.008	
Н	0.15	0.31	0.006	0.012	

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
A	2.3	0.091
В	2.5	0.098
С	4.3	0.169
D	1.8	0.071
Е	6.8	0.268

MARKING DIAGRAM



P/N = Marking Code
G = Green Compound
YW = Date Code
F = Factory Code



Taiwan Semiconductor

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.